

L Number	Hits	Search Text	DB	Time stamp
-	226	semiconduct\$3 and HMD\$ with prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/19 18:13
-	2005	semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:16
-	10	((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMD\$ or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 18:47
-	6246	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:03
-	1152	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:21
-	12	((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)) and ((develop\$4 or rins\$3) or (spin\$4 or rotat\$3 or turn\$3 or speed\$3)) same (exhaust\$3 or air) near\$ (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:10
-	130	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near\$ (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:22
-	11	((((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near\$ (velocit\$3 or speed\$3)) and ((develop\$4 or rins\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near\$5 (velocit\$3 or speed\$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:24
-	1347	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 08:21

-	179	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 09:22
-	11	((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:06
-	1091	(resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remove\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3);	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:12
-	825	((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remove\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3); and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3); and (semiconduct\$3 or wafer or silicon or "Si"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:15

	320	((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolymer\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/20 17:18
	39	(((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolymer\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:44
	1	("4556785").PN.	USPAT; US-PGPUB	2003/06/21 16:17
	443	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 19:53
	237	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3) or ((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3 same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:06

	85	((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and ((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) near5 vapor) same (seconds or "sec")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/21 20:08
	6097	((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rins\$3 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolymer\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:57

-	721	430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3;) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and (develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$ or pass\$) near5 (velocit\$3 or speed\$3)) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or inert or gas\$4)) and (resist or photoresist or photopolymer\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/23 16:56
-	141	430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3;) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and (develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$ or pass\$) near5 (velocit\$3 or speed\$3)) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or inert or gas\$4)) and (resist or photoresist or photopolymer\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm"))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/24 11:47